

MOSFETs Silicon N-Channel MOS

# **SSM6N357R**

# 1. Applications

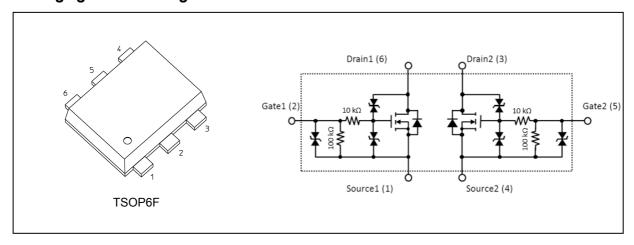
· Relay Drivers

#### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 3.0-V gate drive voltage.
- (3) Built-in Internal Zener diodes and resistors.
- (4) HBM: 2-kV class

Note 1: For detail information, please contact to our sales.

#### 3. Packaging and Pin Assignment





# 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	60	V
Gate-source voltage			$V_{GSS}$	±12	
Drain current (DC)		(Note 1)	I <sub>D</sub>	650	mA
Drain current (pulsed)		(Note 1), (Note 2)	I <sub>DP</sub>	1300	
Power dissipation		(Note 3)	P <sub>D</sub>	1	W
Power dissipation	(t ≤ 10s)	(Note 3)	P <sub>D</sub>	1.5	
Channel temperature			T <sub>ch</sub>	150	°C
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	12.6	mJ
Storage temperature			T <sub>stg</sub>	-55 to 150	ç

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  10  $\mu$ s, duty  $\leq$  1 %
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note 4:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25 °C (Initial state), L = 20 mH

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

# 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 3 \text{ V}$	_	_	±60	μА
			$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$	_	_	±90	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 12 V, V <sub>GS</sub> = 0 V	_	_	0.5	
			V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_	_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60			V
Gate threshold voltage	(Note 1)	V <sub>th</sub>	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	1.3	_	2.0	
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 3 V	_	1.2	2.4	Ω
			I <sub>D</sub> = 150 mA, V <sub>GS</sub> = 5 V	_	0.8	1.8	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	V <sub>DS</sub> = 12 V, I <sub>D</sub> = 150 mA	_	500	_	mS

Note 1: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation, V<sub>GS(ON)</sub> must be higher than V<sub>th</sub>, and V<sub>GS(OFF)</sub> must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 2: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C <sub>iss</sub>	$V_{DS} = 12 \text{ V}$ , $V_{GS} = 0 \text{ V}$ ,	_	43	60	pF
Reverse transfer capacitance		C <sub>rss</sub>	f = 1 MHz	_	2.5	_	
Output capacitance		C <sub>oss</sub>		_	20	_	
Switching time (turn-on time)	(Note 1)	t <sub>on</sub>	$V_{DD}$ = 12 V, $V_{GS}$ = 0 to 3.0 V,	_	990	_	ns
Switching time (turn-off time)	(Note 1)	t <sub>off</sub>	$R_G = 50 \Omega$	_	3000	_	

Note 1: See Chapter 5.3

#### 5.3. Switching Time Test Circuit

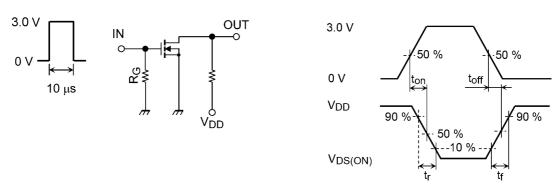


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = 12 V, $I_{D}$ = 650 mA,	_	1.5		nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 5.0 V	_	0.2		
Gate-drain charge	$Q_{gd}$		_	1.2		

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# 5.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = -650 mA, V <sub>GS</sub> = 0 V	_	-0.87	-1.2	V

Note 1: Pulse measurement.

# 6. Marking

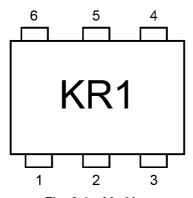


Fig. 6.1 Marking



#### 7. Characteristics Curves (Note)

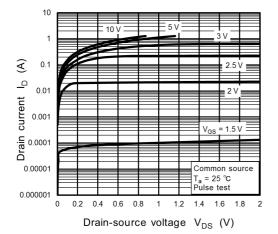


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

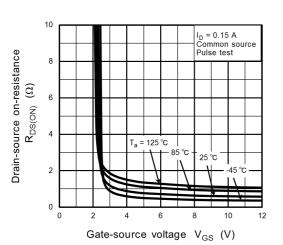


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

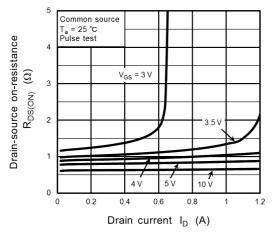


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

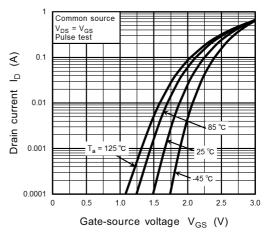


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

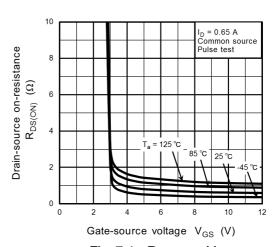


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

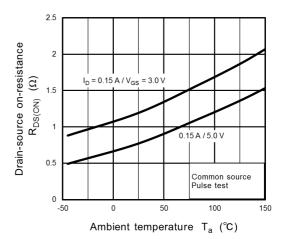
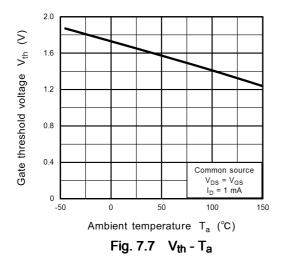
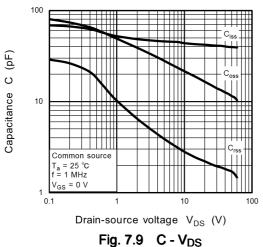
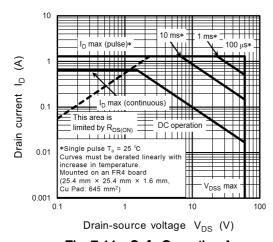


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>











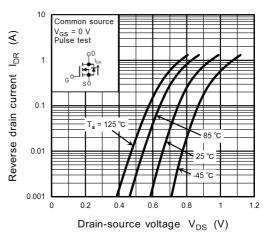


Fig. 7.8 IDR - VDS

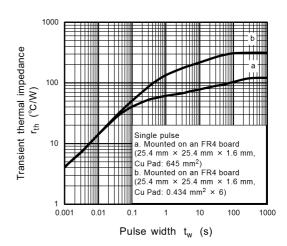


Fig. 7.10 rth - tw

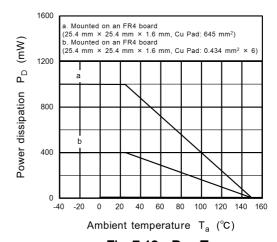


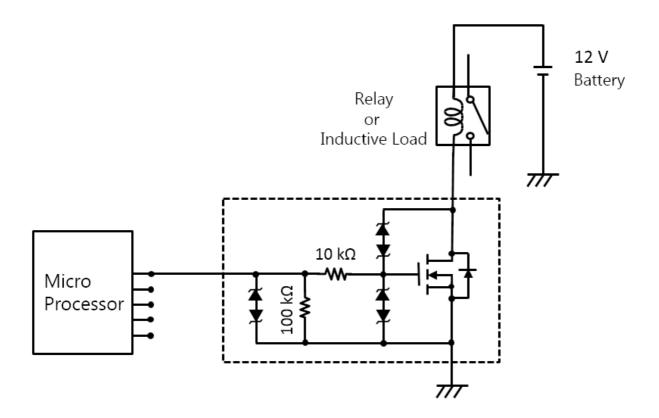
Fig. 7.12 P<sub>D</sub> - T<sub>a</sub>

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.3.0



# 8. Application Information

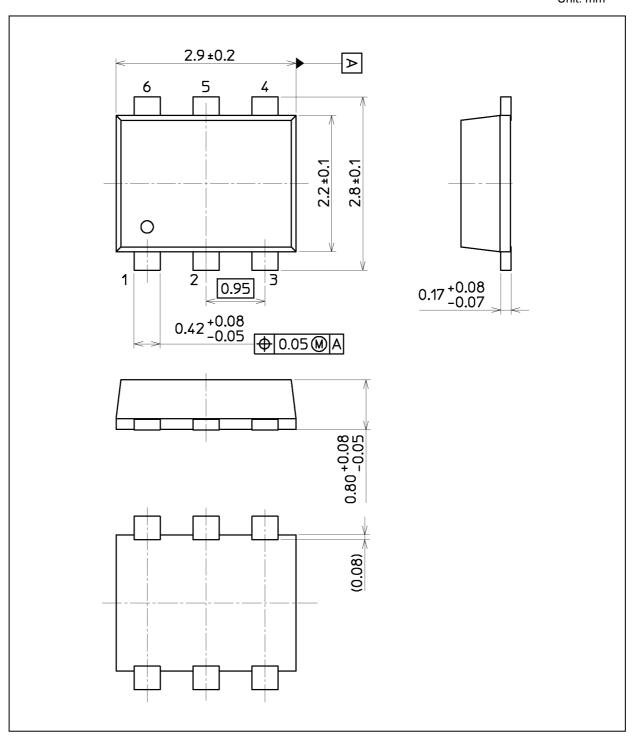


Rev.3.0



# **Package Dimensions**

Unit: mm



Weight: 0.016 g (typ.)

	Package Name(s)
Nickname: TSOP6F	



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